# imall

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



## Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832 Email & Skype: info@chipsmall.com Web: www.chipsmall.com Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



## 4V Drive Nch+Nch MOSFET SP8K24

## Structure

Silicon N-channel MOSFET

## Features

- 1) Built-in G-S Protection Diode.
- 2) Small and Surface Mount Package (SOP8).

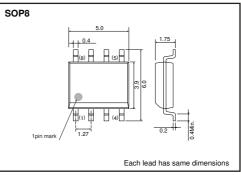
#### Applications

Power switching ,  $\ensuremath{\mathsf{DC}}\xspace$  /  $\ensuremath{\mathsf{DC}}\xspace$  converter , Inverter

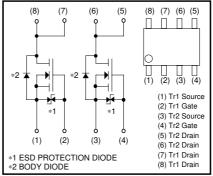
## Packaging dimensions

	Package	Taping		
Туре	Code	ТВ		
	Basic ordering unit (pieces)	2500		
SP8K24		0		

#### •Dimensions (Unit : mm)



### Equivalent circuit



A protection diode is included between the gate and the source terminals to protect the diode against static electricity when the product is in use. Use the protection circuit when the fixed voltages are exceeded.

### ● Absolute maximum ratings (Ta=25°C)

<It is the same ratings for the Tr1 and Tr2.>

Parameter		Symbol	Limits	Unit
Drain-source voltage		V <sub>DSS</sub>	45	V
Gate-source voltage		V <sub>GSS</sub>	±20	V
Drain current	Continuous	I <sub>D</sub>	±6.0	A
	Pulsed	I <sub>DP ∗1</sub>	±24	A
Source current (Body diode)	Continuous	ls	1	A
	Pulsed	I <sub>SP ∗1</sub>	24	А
Total power dissipation		P <sub>D</sub> ∗ <sub>2</sub>	2	W / TOTAL
		FD *2	1.4	W / ELEMENT
Chanel temperature		T <sub>ch</sub>	150	°C
Range of Storage temperature		T <sub>stg</sub>	-55 to +150	°C

\*1 PW  ${\leq}10\mu\text{s}$  , Duty cycle  ${\leq}~1\%$ 

\*2 Mounted on a ceramic board

## Transistor

## •Electrical characteristics (Ta=25°C)

< It is the same characteristics for the Tr1 and Tr2.>

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	Igss	-	-	±10	μA	$V_{GS}=\pm 20V, V_{DS}=0V$
Drain-source breakdown voltage	V(BR) DSS	45	-	-	V	I <sub>D</sub> = 1mA, V <sub>GS</sub> =0V
Zero gate voltage drain current	IDSS	_	-	1	μA	VDS= 45V, VGS=0V
Gate threshold voltage	V <sub>GS (th)</sub>	1.0	-	2.5	V	V <sub>DS</sub> = 10V, I <sub>D</sub> = 1mA
	RDS (on)*	-	18	25	mΩ	I <sub>D</sub> = 6.0A, V <sub>GS</sub> = 10V
Static drain-source on-state resistance		-	24	34	mΩ	I <sub>D</sub> = 6.0A, V <sub>GS</sub> = 4.5V
resistance		-	26	37	mΩ	ID= 6.0A, VGS= 4.0V
Forward transfer admittance	Y <sub>fs</sub> *	6.0	-	-	S	V <sub>DS</sub> = 10V, I <sub>D</sub> = 6.0A
Input capacitance	Ciss	-	1400	-	pF	V <sub>DS</sub> = 10V
Output capacitance	Coss	-	310	-	pF	V <sub>GS</sub> =0V
Reverse transfer capacitance	Crss	-	175	-	pF	f=1MHz
Turn-on delay time	td (on) *	-	19	-	ns	VDD≒25V
Rise time	tr *	-	30	-	ns	ID= 3.0A Vgs= 10V
Turn-off delay time	td (off) *	-	72	-	ns	$R_{L} = 8\Omega$
Fall time	tr *	_	27	-	ns	R <sub>G</sub> =10Ω
Total gate charge	Qg *	_	15.4	21.6	nC	V <sub>DD</sub> ≒25V, V <sub>GS</sub> =5V
Gate-source charge	Q <sub>gs</sub> *	-	3.7	-	nC	I <sub>D</sub> = 6.0A
Gate-drain charge	Q <sub>gd</sub> *	_	6.5	-	nC	$R_{L}=4\Omega, R_{G}=10\Omega$

\*Pulsed

## ●Body diode characteristics (Source-drain) (Ta=25°C)

< It is the same characteristics for the Tr1 and Tr2.>

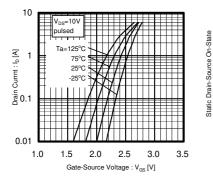
Parameter	Symbol	Min.	Тур.	Max.	Unit	Condition
Forward voltage	V <sub>SD</sub> *	_	_	1.2	V	I <sub>S</sub> =6.0A/V <sub>GS</sub> =0V

\* pulsed

2/4

## Transistor

#### Electrical characteristic curves





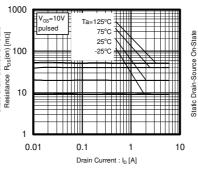


Fig.2 Static Drain-Source On-State Resistance vs. Drain Current (1)

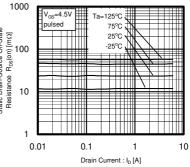


Fig.3 Static Drain-Source On-State Resistance vs. Drain Current (2)

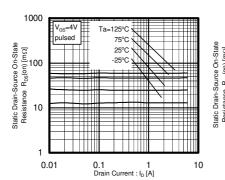


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current (3)

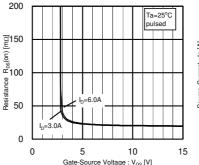
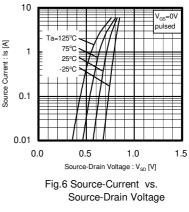
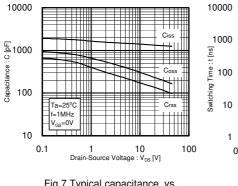
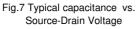
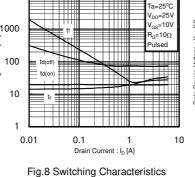


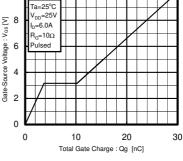
Fig.5 Static Drain-Source On-State Resistance vs. Gate-Source Voltage











10



3/4

## Transistor

## Measurement circuits

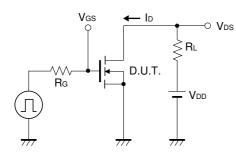


Fig.10 Switching Time Test Circuit

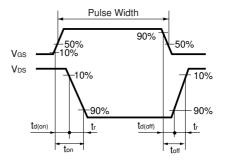


Fig.11 Switching Time Waveforms

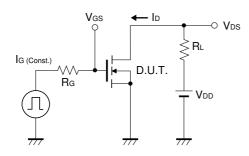
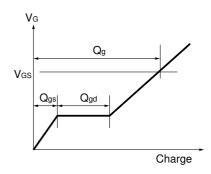


Fig.12 Gate Charge Test Circuit





### Notes

- No technical content pages of this document may be reproduced in any form or transmitted by any means without prior permission of ROHM CO.,LTD.
- The contents described herein are subject to change without notice. The specifications for the
  product described in this document are for reference only. Upon actual use, therefore, please request
  that specifications to be separately delivered.
- Application circuit diagrams and circuit constants contained herein are shown as examples of standard use and operation. Please pay careful attention to the peripheral conditions when designing circuits and deciding upon circuit constants in the set.
- Any data, including, but not limited to application circuit diagrams information, described herein are intended only as illustrations of such devices and not as the specifications for such devices. ROHM CO.,LTD. disclaims any warranty that any use of such devices shall be free from infringement of any third party's intellectual property rights or other proprietary rights, and further, assumes no liability of whatsoever nature in the event of any such infringement, or arising from or connected with or related to the use of such devices.
- Upon the sale of any such devices, other than for buyer's right to use such devices itself, resell or
  otherwise dispose of the same, no express or implied right or license to practice or commercially
  exploit any intellectual property rights or other proprietary rights owned or controlled by
- ROHM CO., LTD. is granted to any such buyer.
- Products listed in this document are no antiradiation design.

The products listed in this document are designed to be used with ordinary electronic equipment or devices (such as audio visual equipment, office-automation equipment, communications devices, electrical appliances and electronic toys).

Should you intend to use these products with equipment or devices which require an extremely high level of reliability and the malfunction of which would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), please be sure to consult with our sales representative in advance.

It is our top priority to supply products with the utmost quality and reliability. However, there is always a chance of failure due to unexpected factors. Therefore, please take into account the derating characteristics and allow for sufficient safety features, such as extra margin, anti-flammability, and fail-safe measures when designing in order to prevent possible accidents that may result in bodily harm or fire caused by component failure. ROHM cannot be held responsible for any damages arising from the use of the products under conditions out of the range of the specifications or due to non-compliance with the NOTES specified in this catalog.

Thank you for your accessing to ROHM product informations. More detail product informations and catalogs are available, please contact your nearest sales office.

## **ROHM** Customer Support System

THE AMERICAS / EUPOPE / ASIA / JAPAN

## www.rohm.com

Contact us : webmaster@rohm.co.jp

Copyright © 2007 ROHM CO.,LTD. ROHM CO., LTD. 21, Saiin Mizosaki-cho, Ukyo-ku, Kyoto 615-8585, Japan TEL : +81-75-311-2121 FAX : +81-75-315-0172

Appendix1-Rev2.0

rohm